Random Variation in Nanoscale HfZrO₂ Ferroelectric FinFETs: Physical Origin and Neuromorphic System Implications

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Abstract

This paper unveils the impact of random phase distribution fomented variations on the characteristics of hafnium zirconium oxide (HZO) based ferroelectric FETs, and the implications towards the application in neuromorphic system. TiN/HZO/TiN/SiO₂ ferroelectric capacitors are fabricated on silicon substrate. Statistical distribution of coercive voltage from polarization-voltage measurements show a two-peak distribution, which is attributed to the existence of two distinct groups of samples – ferroelectric-dominant and paraelectric-dominant ones. Such distinction is likely due to the incompleteness of nucleation-based orthorhombic crystal phase formation in the paraelectric-dominant samples. Subsequently, ferroelectric FinFET devices with single and multiple fins have been fabricated on SOI wafer using a gate first process, with gate lengths down to 40nm. Ferroelectric hysteresis with enhanced static memory window up to 3.5V in 10nm HZO based ferroelectric FET is observed. Short-channel multiple-fin devices show particularly good ferroelectric switching characteristics and high yield. In addition, these devices show highly linear and symmetric multi-level programming characteristics, which makes them an excellent candidate as synaptic device. Modelling of device-to-device and cycle-to-cycle variation is performed based on measured data and applied to system level neural network simulations using the CIMulator software platform. Device-to-device variation is mostly compensated during neural network online training and has virtually no impact on inference accuracy. On the other hand, cycle-to-cycle threshold voltage variation up to 400mV can be tolerated for MNIST handwritten digits recognition. An online training accuracy of 96.34% can be achieved given the measured variability. We further demonstrate the optimization of inference-mode gate voltage considering ferroelectric FET based neural network.

Keywords: ferroelectric, FinFET, neuromorphic, variation

1. Introduction:

CMOS-compatibility of HfₓZr₁₋ₓO₂ (HZO) makes the HZO-based ferroelectric FinFETs an excellent candidate for logic [1], memory, and neuromorphic devices due to its superior endurance and write speed as compared to Flash, significantly higher on-to-off current ratio than MRAM, as well as negligible impact from random telegraphic noise due to charge-based operation, unlike RRAM [1–5]. The pivotal issue, however lies in the innate stochastic trait due to random phase distribution in HZO crystal, as well as traps which may capture electrons or holes from the channel side (CS) or gate side (GS) [6–9]. These effects infuse serious reliability issues in terms of degradation of endurance [10-11] in deeply scaled HZO based ferroelectric FET (Fe-FET) devices as well as memory window (MW) variation across devices.

In the first part of this paper, we describe the fabrication, characterization, and analysis of ferroelectric capacitors and FinFETs, and provide a physical explaination for device
variability. Ferroelectricity is known to be a crystal structure dependent property engendered from the polarization catastrophe [12–15], which results from the instability of crystal structure.

The noncentrosymmetric $Pca_2_1$ orthorhombic phase of HZO is responsible for ferroelectricity in HZO. The other phases like cubic or monoclinic symmetry does not show ferroelectricity. Therefore, it is essential to form the orthorhombic phase in HZO film to instigate the ferroelectric switching. Usually, hafnium oxide is doped with Si, Al or even ZrO$_2$ and subjected to high temperature annealing under various conditions to stabilize the ferroelectric orthorhombic phase[17-20]. Despite the adoption of these stabilization techniques, atomic-layer-deposited FE HZO films exhibit non-uniform crystal properties, which can be observed from the fourier transform of TEM micro-graph of HZO films (Fig. 1(a)).

We further observed the plethora of ferroelectric domains in multifin FET devices. The hysteresis in Fe-FETs is the result of interplay between trap-assisted switching and ferroelectric switching. The net hysteresis is the difference of hysteresis produced by traps and FE domains. The presence of profuse number of ferroelectric domains helm the hysteresis in counter clockwise (CCW) direction in n-type Fe-FET, whereas scarcity of FE domains make the device switching trap dominant or clockwise (CW)[6]. We observe that almost 90% of multifin devices show CCW switching, whereas a mere 10% single fin devices showed CCW switching. Larger HZO film area in multifin devices causes higher nucleation probability and therefore more rapid formation of FE crystal.

In the second part of this paper, we evaluate the impact of experimentally observed device-to-device and cycle-to-cycle variation on neuromorphic systems. Neural network training simulation is performed using the CIMulator [21] software platform to fathom the effects of the aforementioned variations in Fe-FETs towards neuromorphic application. For inference-only (offline training) applications, Fe-FETs form a memory array to perform computing-in-memory (CIM) tasks.

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**Fig. 1.** (a) Fourier transform (FT) of high-resolution TEM image of HZO deposited as gate insulator. The FT images and d-spacing variation across 5 locations within a single FeFET device highlights the non-uniformity of poly-crystalline HZO. (b) Polarization-voltage curve of ferroelectric capacitors. (c) Maximum capacitance vs average coercive voltage. With increasing coercive voltage, the maximum capacitance decreases. (d) Equivalent sub-circuit model showing the effect of paraelectric phase inside the HZO film ($C_{para}$) in modulating the coercive voltage. (e) The probability density function(PDF) and cumulative density(CDF) of forward and reverse coercive voltages, highlighting the two-peak distribution, which indicates two distinct groups of devices: ferroelectric-dominate and paraelectric-dominant.
It is programmed only one time to store the weight coefficient of neural network, and used for computation such as multiply-and-accumulate (MAC) afterwards without changing weights (memory write). On the other hand, Fe-FETs may also be used for online-training, where the entire neural network is trained in the memory array. This requires constant updating of weight coefficient (memory write) during training. With endurance up to $10^{10}$ demonstrated for HZO films[22] such application is plausible. Device-to-device variation is expected to play an important role for inference-only applications, whereas cycle-to-cycle variation, physically originating from random telegraphic noise, is expected to play an important role for both inference-only and online training applications.

2. **HZO Ferroelectric Capacitor Fabrication and Variability Characterization:**

HZO FE capacitors have been fabricated to investigate the material property and its statistical behavior. We started with an n+ silicon wafer and performed dry-oxidation to form a 2nm-thick interfacial layer of SiO$_2$ on top of silicon to block trapping of electrons from silicon towards the intrinsic defect sites in HZO. The bottom TiN electrode has been deposited by physical vapour deposition (PVD) on top of SiO$_2$. Subsequently, the 10nm HZO insulator and the top TiN electrodes are deposited by atomic layer deposition (ALD) and PVD, respectively. HZO is subjected to rapid thermal annealing (RTA) for 30s at 700ºC to facilitate orthorhombic $Pc2_1$ crystal formation in the presence of capping top TiN electrode. Finally, the capacitors are patterned and etched with an active area of 1000μm$^2$.

Fig. 1(b) shows the measured polarization v.s. voltage (P-V) characteristics of the HZO capacitors, where coercive voltage($V_c$) and remnant polarization($P_r$) have been shown. The coercive voltage($V_c$) or the depolarization voltage is the voltage required to flip the polarization from any state to zero and the remnant polarization($P_r$) is polarization at zero applied voltage[23]. We clearly see in Fig. 1(b) an increase in coercive voltage when the saturation polarization($P_s$) decreases. Such trend is also reflected in Fig. 1(c), which shows that the maximum capacitance ($C_{\text{max}}$) decreases with increasing average coercive voltage ($V_c^{\text{avg}}$). The inset of Fig. 1(c) shows a typical measured capacitance v.s. voltage (C-V) curve of Metal(TiN)-Ferroelectric(HZO)-Metal(TiN) stack with low paraelectric phase density. The well defined peaks in the C-V curve substantiate the existence of ferroelectricity in the stack. The capacitance at those two peaks are defined as $C_{\text{peak}^+}$ and $C_{\text{peak}^-}$. $C_{\text{max}}$ is defined as max($C_{\text{peak}^+}$, $C_{\text{peak}^-}$)/$C_{\text{SiO}_2}$. Theoretically, the measured total capacitance in Fig. 1(c) can be expressed as three capacitances in series:

$$\frac{1}{C_{\text{meas}}} = \frac{1}{C_{\text{FE}}} + \frac{1}{C_{\text{para}}} + \frac{1}{C_{\text{SiO}_2}} = \frac{1}{C_{\text{HZO}}} + \frac{1}{C_{\text{SiO}_2}}$$

where $C_{\text{SiO}_2}$ is a linear constant capacitance due to the 2nm SiO$_2$ layer; $C_{\text{FE}}$ is the non-linear voltage dependent ferroelectric capacitance. $C_{\text{para}}$, on the other hand, accounts for the voltage independent paraelectric layer capacitance, which varies from device to device due to stochastic domain distribution (i.e. each domain has different effective paraelectric layer thickness). A trend of decreasing $C_{\text{meas}}^{\text{max}}$ with increasing $V_c^{\text{avg}}$ is explained as follows. The linear capacitor, engendered from the paraelectric phase of HZO, is in series with ferroelectric capacitor inside HZO. Taking parallel plate assumption for simplicity($C_{\text{para}} = \frac{\varepsilon A}{d}$), when the effective thickness of paraelectric phase (Fig.1(d)) increases, the net capacitance in HZO decreases ($C_{\text{HZO}} = \frac{C_{\text{para}}C_{\text{FE}}}{C_{\text{para}}+C_{\text{FE}}}$), and the voltage drop across the paraelectric region increases. As a result, $V_c^{\text{avg}}$ as measured externally increases, since larger external voltage is required to reverse the polarization of the FE layer(assuming the ferroelectric properties are unchanged as paraelectric region thickens). At the same time $C_{\text{max}}$ decreases due to smaller $C_{\text{para}}$. Fig. 1(d) shows a sub-circuit model of HZO, which accounts for the co-existence of paraelectric and ferroelectric capacitors.

The variability in Fe-FET devices is also due partly to the existence of $C_{\text{para}}$, as the thickness ratio of co-existing paraelectric and ferroelectric layers are random. The switching dynamics of nanoscale FE capacitors shows that polarization switching in nanoscale capacitors occurs only at predetermined sites within the crystal [24]. Switching begins with a single nucleation events and does not follow the Kolmogorov-Avrami-Ishibashi (KAI) model of nucleation and growth [24]. Therefore it is important to create predetermined switching sites or orthorhombic crystal sites, where the nucleation event can occur.

The PDF and CDF of positive and negative coercive voltages ($V_{c^+}$ and $V_{c^-}$) indicate the existence of two distinct phases in HZO film, as illustrated in Fig. 1(e). During the annealing process HZO undergoes phase transition to orthorhombic phase. The energy required for such transition is obtained from the externally applied temperature and pressure during RTA. If the total energy is not sufficient some parts of HZO remain paraelectric. The two-peak distribution indicates a nucleation-based growth. Sufficient time is required for the random nucleation event to occur. Once it does and an orthorhombic crystal “seed” forms, it quickly propagates through the entire film in the device so that it transforms from paraelectric-dominant to ferroelectric-dominant. This leads to two distinct groups of devices – paraelectric and ferroelectric, when nucleation time is limited. Although, a high coercive voltage may sound alluring for memory operations, the stochasticity arising from the variations in coercive voltage is not desired. These variations will result in non-uniformity of the threshold voltage of Fe-FET devices with same dimensions, leading to ambiguity in
program and erase operations. Longer post-deposition annealing may alleviate such variation, as it allows more time and therefore higher probability for orthorhombic crystal “seed” to form. In the following sections the effects of such variations on the memory window (MW) and program-erase operations are discussed and its impact on neuromorphic computing systems is quantified.

3. Tri-gate Ferroelectric FinFET Nanofabrication and Multi-level Characterization:

Nanoscale n-type and p-type tri-gate ferroelectric FinFETs are fabricated on SOI wafer, with gate length as low as 40nm [27]. Fig. 2(a) shows the schematic of the fabricated device. Fig. 2(b) shows the transmission electron micrograph of one of the devices.

The electrical characterization of the devices were done in two steps, using Agilent B1500A Semiconductor Analyzer with B1530A arbitrary waveform generation and measurement unit. First, double-sweep DC characterization was performed by slowly varying the gate voltage from -3V to 3V, and then back to -3V, at a constant drain voltage of 100mV. The Igs-Vgs characteristics were analyzed to understand whether the switching characteristics were dominated by ferroelectric domains or traps. Subsequently, the devices were subjected to 1µs-wide pulses with various (positive or negative) pulse amplitudes, for characterizing its dynamic behavior, including its response to program and erase operation, multilevel programming behavior, symmetry and linearity.

3.1 DC Characterization:

The threshold voltage was extracted at constant 200nA drain current for both forward and reverse sweep. Fig. 2(c) shows the DC Igs-Vgs characteristics of an n-type device, with 50nm Lg and 10nm TF. The static memory window (MW), defined as the difference of forward and reverse threshold voltages, is 3.5V. This is beyond the maximum theoretical limit of 2V for Fe-FET with 10nm HZO [16,18]. The large
MW is likely due to the increase of external coercive voltage due to the presence of paraelectric phase, as discussed in the previous section. Apart from the effect of undesired paraelectric phase, the trapping from gate side (GS) may also reinforce the hysteresis of Fe-FET in the same direction as FE switching [6]. However, the pA-range gate current in our devices obliterates the possibility of GS trapping and de-trapping. Therefore, we are left with only other possible explanation of paraelectric phase, originating from incomplete formation of ferroelectric (orthorhombic) phase in HZO.

Note that while most multi-fin ferroelectric FinFET device show a reasonable static MW from DC measurements (Fig. 2(d)), that is not the case for single-fin devices. This is consistent with the analysis in the previous section. Since ferroelectric polarization change is a nucleation-based phenomenon, multi-fin device with larger area (HZO films in all fins are connected) has greater chance of containing a “seed” for polarization change. Thus most multi-fin device show CCW hysteresis, which indicated ferroelectricity. On the other hand, it is quite likely for single-fin devices to be absent of any such “seed” therefore most single-fin devices show CW hysteresis, or trap-dominant behavior, without ferroelectricity.

Although the wide MW seems to be an alluring option to increase the noise margin of Fe-FETs, the presence of paraelectric phase is erratic, making the coercive voltage distributed over a wide range from ±1V to ±2.5V. The wide distribution of MW, forward threshold voltage ($V_{th}^{fw}$) and reverse threshold voltage ($V_{th}^{rvs}$) makes program and erase operations unstable. Fig. 2(d) shows the variation of MW with gate length. Although the short-channel devices show better (higher) MW than long channel, the variation is also high. This is typical for scaled devices which is more susceptible to short channel effects. This trait has already been reported in several publications [10,26]. Fig. 2(c) shows device to device variation of $V_{th}^{fw}$ and $V_{th}^{rvs}$ of fabricated devices at 50nm gate length. This stochastic switching of deeply scaled Fe-FET generated from the random distribution of ferroelectric and paraelectric phase has been a pivotal issue for deploying it in mass production.

Although the device to device variation is quite high due to the random distribution of paraelectric and ferroelectric phase in HZO, cycle to cycle variations is not affected by the presence of paraelectric phase. The cycle to cycle variation of $V_{th}^{fw}$ and $V_{th}^{rvs}$ is likely due to random telegraphic noise, which originates from trapping and de-trapping events in intrinsic defect sites in HZO. We have measured negligible cycle to cycle read variations by using slowly varying gate voltage for all of our devices (Fig. 2(f)) up to 40 cycles.

In the next sections we shall discuss the effect of such stochastics distribution of ferroelectric domains as well as cycle-to-cycle noise on program and erase charactereristics and neuromorphic applications.

### 3.2 Binary Program and Erase Behavior:

Although the static MW, described in previous section gives us a qualitative idea about the behavior of FeFET, the dynamic MW or noise margin between two states of Fe-FET is obtained by fast pulse-program and pulse-erase operations vary vastly from the static MW [28-34]. The static MW, which can be written by $2 \times E_C \times t_{FE}$ [25], provides the theoretical upper limit of the noise margin. For practical applications this value is greatly affected by trapping, random distribution of ferroelectric-paraelectric domains and also on the programming scheme used to program and erase the device. Therefore, the dynamic MW is an important behavior to study due to its relevance towards real write operations in memory applications.

![Fig. 3. (a) Program and erase scheme for binary states. FinFET cross-section view of (b) Low $V_{th}$ State (c) High $V_{th}$ State (d) Dynamic MW or noise margin of 2.24V was achieved during pulse-program and pulse-erase operations.](attachment:image.png)

Fig. 3 shows the binary operations. We began with a pristine FeFET device and programmed it to low threshold voltage state by applying 8V pulse of width 1μs as shown in Fig. 3(a) (the breakdown voltage for multifin devices were around 9V). The positive pulse changes the remnant polarization in HZO, which changes the channel conductance and threshold voltage by infusing extra channel charge in the Si fin (Fig. 3(b)). The threshold voltage was extracted at constant drain current of 200nA from a $I_d-V_{gs}$ sweep. $V_{gs}^{sta}$ is the lower limit of the gate voltage for read $I_d-V_{gs}$ sweep. Note that negative starting sweep voltage after positive program...
pulse fosters de-trapping so that charge-trapping behavior is minimized and we may focus on the FE phenomenon. One must also note the $V_{g}^{var}$ must not alter the memory state of the device by depolarizing the HZO. To ensure this $V_{g}^{var}$ was kept constant and the following condition given by equation (2) must be satisfied.

$$|V_{g}^{start}| \leq |V_{pgm}|$$

The details of this characterization conditions and the method has been discussed in one of our previous publication [36]. Later, we have applied one -8V pulse with 1μs width to erase the Fe-FET or to drive the Fe-FET device to high threshold voltage state. Upon application of negative pulse, the polarity of the remnant charges is inverted, which upends the device to accumulation state (Fig. 3(c)). Therefore, the threshold voltage is increased. We have obtained a reasonable difference of 2.24V in threshold voltage between program and erase states. In addition, one can use wider pulse of same amplitude for achieving higher noise margin (or MW), as it has been seen in literature that both pulse width and amplitude change the polarization state [5]. The drain of the devices was kept at 0V during the write operation and at 100mV during read operations. For sanity check we performed read and write operations at various drain voltages (50mV, 100mV, 300mV and 1V) and noticed that DIBL or drain voltage does not affect the dynamic MW or the noise margin of the devices significantly.

### 3.3 Multilevel Operation for Neuromorphic Application and Compact Modeling:

In order to obtain long term potentiation (LTP) and long term depression (LTD) characteristics for neuromorphic applications, we have applied 1μs-wide pulse of increasing (0.2V to 8V with a step of 0.2V) and decreasing (-0.2V to -8V with a step of -0.2V) amplitudes to partially polarize the HZO stack in Fe-FET (Fig. 4). The drain voltage was kept at 0V during the programming operation. Each set (potentiation or depression) pulse was preceded by a reset pulse (±8V) to drive the conductance back to the starting point. The incrementing amplitude in each step increments the remnant polarization of HZO film by a small amount, which inevitably changes the threshold voltage and channel conductance of the Fe-FET. The domain formation in ferroelectric material is of similitude to crack propagation in solids [35] and it is quite well-known fact from the literature [36] that if reset pulse is applied, program pulses of similar amplitude cannot change the polarization state of the ferroelectric. This necessitates the application of pulses with higher amplitude. Immediately after each programming pulse the read of the memory state of the device was accomplished. During the read operation the drain was kept at constant 100mV and a ramp voltage was applied at gate terminal. The ramp magnitude was varied during the read operations in a similar manner as [37] for eradicating the trapping in HZO film. The conductance was extracted from the $I_{d}$-$V_{g}$ curve of LTP and LTD operations at a specific gate voltage (Fig.5.a, Fig.5.b). We have used various gate voltage of values 0V, 0.25V, 0.5V, 0.75V, 1V and 1.25V to extract the conductance. In the next section we have discussed the impact of the gate voltage on the number of conductance state.

![Fig. 4. LTP-LTD pulse scheme. A full (±8V) program/erase pulse precedes each LTP/LTD pulse to ensure stable program/erase operation.](image-url)

![Fig. 5(a) $I_{d}$-$V_{g}$ curve during LTP](image-url)

![Fig. 5(b) $I_{d}$-$V_{g}$ curve during LTD](image-url)

![Fig. 5(c) Threshold voltage modulation during LTP-LTD](image-url)

![Fig. 5(d) Conductance variation during LTP-LTD](image-url)
Fig. 5(a) shows the LTP characteristics obtained by 1μs-wide increasing pulses and Fig. 5(b) shows the LTD characteristics obtained by pulses of the opposite polarity. Fig. 5(c) shows the highly linear and symmetric threshold voltage modulation traits obtained by partial polarization of ferroelectric stack in a Fe-FET with gate length 50nm. We have applied a total of 26 positive and gradually increasing pulses for LTP and 26 negative and gradually decreasing pulses for LTD. Each pulse changes the remnant polarization of the HZO stack, which changes the threshold voltage of the device, engendering a new memory state. Thus, we have obtained a total of 26 memory states excluding the initial states.

Fig. 5(d) shows the gradual change in channel conductance during LTP and LTD. The channel conductance is modeled according to one of our previous publication [36]:

\[
G = \frac{KV_{\text{gateff}}}{1 + UA(V_{\text{gateff}} + \Delta)E + R_{\text{ds}} + KV_{\text{gateff}} + UD\frac{V_{\text{gateff}}^2}{V_D}}
\]

The model is based on industry standard BSIM4 model, where the term \(V_{\text{gateff}}\) denotes the effective gate overdrive voltage. UA, EU and \(\Delta\) accounts for the vertical field dependent mobility degradation, and the drain to source series resistance effect is implemented by \(R_{\text{ds}}\). The term UD accounts for coulomb scattering. The details of this model has been described in [37] and this model shows only 1.4% r.m.s error from the measured data[37].

Although the number of threshold voltage states are invariant with read gate voltage (\(V_{\text{g read}}\)), the number of available conductance states highly depends on \(V_{\text{g read}}\).

Primarily, if \(V_{\text{g read}}\) is too low, most of the operational range will fall within the SUB-threshold region (below 200nA) and do not count as distinct states. Fig. 6 shows that the number of distinct conductance states as a function of \(V_{\text{g read}}\). At the same time, however, the on-off ratio will be degraded when \(V_{\text{g read}}\) is too high. Equation (2) may be used for obtaining and optimal \(V_{\text{g read}}\). In the next section, we shall discuss about such trade-off.

4. Implications of Nano-scale Variations on Neuromorphic Applications:

To quantify the impact of variations in Fe-FETs, system level neuromorphic simulation has been performed. The modelled LTP and LTD characteristics along with experimentally calibrated device to device and cycle to cycle variations or the standard deviation (\(\sigma_{\text{D2D}}, \sigma_{\text{C2C}}\)) in \(V_{\text{th}}\) distribution have been used to train a Fe-FET-based multilevel perceptron (MLP) based neural network with MNIST data set [38]. The layers of the neural network is illustrated in Fig. 7(a). Fig. 7(b). shows the implementation of ferroelectric devices as pseudo cross-bar synaptic memory array[5] for the neuromorphic simulation in our CIMulator platform[21]. The experimentally calibrated device to device variation and cycle to cycle variation has a Gaussian distribution with standard deviation in threshold voltage of \(\sigma_{\text{D2D}} = 0.57833\) V and \(\sigma_{\text{C2C}} = 0.0177\) V, respectively. We observed that despite both \(V_{\text{th}}^{\text{fwd}}\) and \(V_{\text{th}}^{\text{rvs}}\) for the Fe-FET getting affected by variation, the difference \(V_{\text{th}}^{\text{fwd}} - V_{\text{th}}^{\text{rvs}}\) remain unchanged. The CIMulator [21] platform is used to estimate system-level accuracy for a given device characteristics and statistical distribution. Two scenarios are considered. The first scenario is online training, wherein 60,000 MNIST image samples are used to train the hardware neural network as illustrated in Fig. 7. Backpropagation algorithm was adopted for training, with a batch size of 600. In the online training scenario, device-to-device variation (\(\Delta V_i\)) for each device is fixed at the very beginning of training, and remains unchanged throughout the training process. For cycle-to-cycle variation, on the other hand, \(\Delta V_i\) changes randomly during read or write throughout the training process for each device in each cycle. The second scenario is offline training, wherein neural network weight coefficients are pre-trained in software (without considering hardware-related variation). The weights are subsequently written into hardware. Such hardware neural network will operate differently from software with errors due to device-to-device variation. In this case, there is no chance for the neural network to have its weight adjusted to compensate hardware-related device-to-device variation.
The online training simulation of Fe-FET based synaptic arrays shows that the accuracy drops as device to device variations are pruned away by the weight adjustment during the continuous training process. There is very little accuracy degradation (Fig. 8(a)). Even though, in principle cycle to cycle variation cannot be absorbed via neural network weight change, its impact is very small due to the mere 17.7mV variation. However, the degradation in performance in terms of accuracy becomes acute in the offline training scenario. The accuracy was dropped from 97.46% to 90.26% by device to device variation alone. The cumulative effect of device to device and cycle to cycle variation deteriorates the recognition accuracy down to 46.81%. Such non-linear behavior is a distinct characteristics of neural networks. When variability is small within a certain threshold, added cycle to cycle variation has little impact. But once such threshold is reached, the small randomness of 17.7mV has a salient effect to degrade system accuracy.

Fig. 7. (a) MLP architecture considered during neuromorphic simulation in Cimulator platform. (b) Deploying Fe-FET as analog synaptic memory array in a simple single layer perceptron[cite drc].

Fig. 8. (a) The impact of variations on training accuracy is minimal for hardware-calibrated variability for the online training scenario, but is significant for the offline training scenario. (b) Impact of device to device variations is large only for offline-trained neural networks. (c) Impact of cycle to cycle variations cannot be compensated by online training. Hardware suggests its effect is small.

Fig. 8(b) highlights the fact that online training is very useful toward the robustness of neural networks in the presence of device-to-device variation. For example, with 10% high intrinsic maximum conductance for a given device, the training algorithm automatically adjusts the synaptic device to be trained to a higher $V_i$, which reduces the conductance by 10% to compensate the variation. That is not the case for offline training. In fact, the accuracy drops below 90% while the device to device variation exceeds 250 mV. Unfortunately, online training cannot fully compensate cycle to cycle variation, as this variation source change from cycle to cycle (Fig. 8(c)). Accuracy quickly degrades as cycle to cycle variation becomes larger. A 400 mV variation brings down the accuracy to 90% during training process. Fortunately, our hardware measurements show that cycle to cycle variation is only 17.7mV so that accuracy degradation is minimal. It’s worth noting that in CIMulator we have adopted the accumulated weight updated method [39] to train the neural network. It is a methodology similar to Σ-Δ modulation method, which saves weight residue for each training cycle to compensate
the insufficient weight resolution. It shows good immunity towards low precision and number of states. The downside, however, is the necessity of additional circuits to store the residue portion of the weights, which are not yet written to hardware.

In Fig. 9(a), we compare accumulate update mode and the conventional linear update mode, where the weight is rounded to the nearest quantization value with residue discarded. The inference accuracy for linear update mode is near 10% (no recognition capability) until the weights have 6 bits or more (>90% accuracy). On the contrary, the accumulated weight update method requires much lower precision, where 97% inference accuracy can be achieved with only two states or 1 bit. As a low read voltage is a prerequisite for low power applications of neural network, the accumulated weight update method is a promising algorithm to train Fe-FET with relaxed requirement for a high read voltage (more number of states).

Although previous researchers have shown multilevel programming in HZO based Fe-FETs [40-43], this is the first testament of dependence of number of conducting states on gate voltage for read, \( V_{g\text{read}} \). Therefore, the impact of the \( V_{g\text{read}} \) on the inference accuracy has been investigated.

Fig. 9(b) shows the impact of read voltage for a specific number of bits. \( V_{g\text{read}} \) as 1V turns out to be the most optimal solution for all four cases shown in the figure. As discussed in the previous section, this read voltage dependency is the result of different on-off ratio of channel conductance at different gate voltage during read operations.

5. Conclusion:

The overall performance of a neuromorphic system is the outcome of confederated performance of device, peripheral circuits, network architecture and algorithm. In this work we fabricated nanoscale HZO FeFET device and analyzed the physical reasons for two main variation sources: (1) paraelectric/ferroelectric phase mixture due to incomplete or insufficient crystallization, which results in device to device variation, and (2) random telegraphic noise due to trapping and de-trapping events, which causes the apparent variation from cycle to cycle. Experiments are underway to mitigate such variability, especially for small devices. We then translate the observed variability to non-ideality in neural network applications. If online training is possible 96.34% for MNIST hand written digits recognition in the presence of variations is achievable. However, offline training may be required due to system constraints, in which case even a moderate device to device variation becomes alarming, and must be mitigated through further material optimization. We concluded that impact of experimentally observed variations on system level accuracy can be made negligible by manipulating the neural network algorithm and architecture.

![Graph](image-url)
### Table-I: Benchmarking with other eNVM and other FeFET Technologies

<table>
<thead>
<tr>
<th>Reference No.</th>
<th>Linearity[5]: $\alpha_p/\alpha_d$</th>
<th>#conductance State</th>
<th>Cycle to cycle variation: $\alpha_{C2C}$</th>
<th>Maximum and Minimum Conductance Ratio: $G_{MAX}/G_{MIN}$</th>
<th>Accuracy</th>
</tr>
</thead>
<tbody>
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<td>[5]</td>
<td>1.75/1.46</td>
<td>32</td>
<td>0.05%</td>
<td>45</td>
<td>90%</td>
</tr>
<tr>
<td>[22]</td>
<td>1.22/1.75</td>
<td>320</td>
<td>N/A</td>
<td>~100</td>
<td>80%</td>
</tr>
<tr>
<td>[44,45]</td>
<td>2.4/-4.88</td>
<td>97</td>
<td>3.5%</td>
<td>12.5</td>
<td>73%</td>
</tr>
<tr>
<td>[46]</td>
<td>1.85/-1.79</td>
<td>102</td>
<td>&lt;1%</td>
<td>2</td>
<td>10%</td>
</tr>
<tr>
<td>[47]</td>
<td>3.68/-6.76</td>
<td>50</td>
<td>&lt;1%</td>
<td>6.84</td>
<td>10%</td>
</tr>
<tr>
<td>[48]</td>
<td>1.94/-0.61</td>
<td>40</td>
<td>5%</td>
<td>4.43</td>
<td>41%</td>
</tr>
<tr>
<td>[49]</td>
<td>0.105/2.4</td>
<td>100-200</td>
<td>1.5%</td>
<td>19.8</td>
<td>87%</td>
</tr>
<tr>
<td>This Work</td>
<td>0.67/-1.13</td>
<td>27</td>
<td>0.4%</td>
<td>45</td>
<td>96.34%</td>
</tr>
</tbody>
</table>

**References:**


[39] Itay Hubara, Matthieu Courbariaux, Daniel Soudry, Ran El-Yaniv, Yoshua Bengio “Quantized Neural Networks: Training Neural Networks with Low Precision Weights and Activations” Journal of Machine Learning Research, 2018